

ICEM100D120W Silicon Carbide Schottky Diode

Product Summary			
I_F	$T_C=123^\circ\text{C}$	100A	Max
V_R		1200V	Min
T_j		175°C	Max
Q_C	V=800V	434nC	Typ

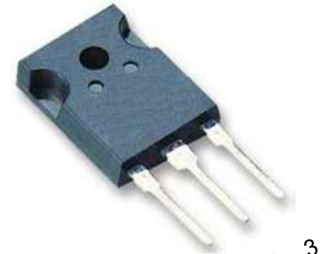
Features

- 1200-Volt Schottky Rectifier
- Zero Reverse Recovery
- Positive Temperature Coefficient on V_F
- Temperature-Independent Switching Behaviour
- Extremely Fast Switching
- Optimized design for high performance power systems

Anode



Cathode



TO247
1:NC, 2:K,
3:A, 4:K
(TO-247)



Lead Free

Maximum ratings^a at $T_j=25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}		1200	V
Continuous Forward Current	I_F	$T_C=25^\circ\text{C}$ $T_C=123^\circ\text{C}$	185 100	A
Non-Repetitive Forward Surge Current, $t_p=10\text{ms}$, Half Sine Wave Pulse	I_{FSM}	$T_C=25^\circ\text{C}$ $T_C=110^\circ\text{C}$	391 365	A
i^2t value $t_p=10\text{ms}$, Half Sine Wave Pulse	$\int j^2 dt$	$T_C=25^\circ\text{C}$ $T_C=110^\circ\text{C}$	764 668	A^2s
Operating Junction Temperature and Storage Temperature	T_j, T_{stg}		-55 to +175	$^\circ\text{C}$

^a Preliminary data sheet - Specifications subject to change.

Parameter	Symbol	Conditions	Values			Unit
			Min	Typ	Max	

Thermal characteristics

Thermal resistance, junction-case	R_{thJC}		-	-	0.23	°C/W
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Electrical characteristics at $T_j=25^\circ\text{C}$, unless otherwise specified

Forward Voltage	V_F	$I_F=100\text{A}, T_j=25^\circ\text{C}$	-	1.53	1.8	V
		$I_F=100\text{A}, T_j=175^\circ\text{C}$	-	2.24	-	
Reverse Current	I_R	$V_R=1200\text{V}, T_j=25^\circ\text{C}$	-	4	10	μA
		$V_R=1200\text{V}, T_j=175^\circ\text{C}$	-	77	-	
Total Capacitive Charge	Q_C	$V=800\text{V}$	-	434	-	nC
Total Capacitance	C	$V_R=0\text{V}, f=1\text{ MHz}$	-	6201	-	pF
		$V_R=400\text{V}, f=1\text{ MHz}$		408		
		$V_R=800\text{V}, f=1\text{ MHz}$		300		

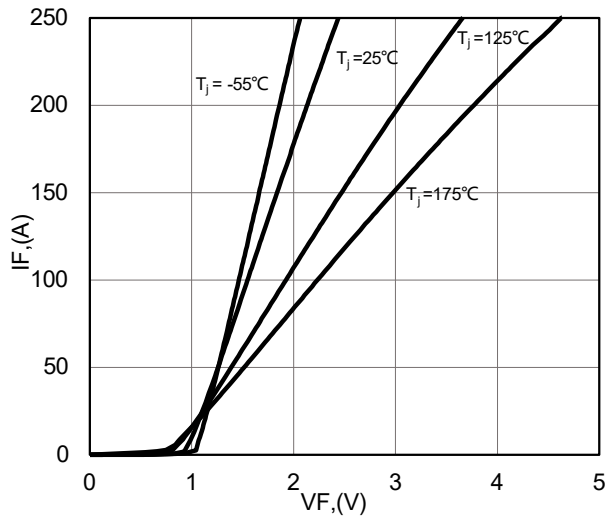


Fig1. Forward Characteristics

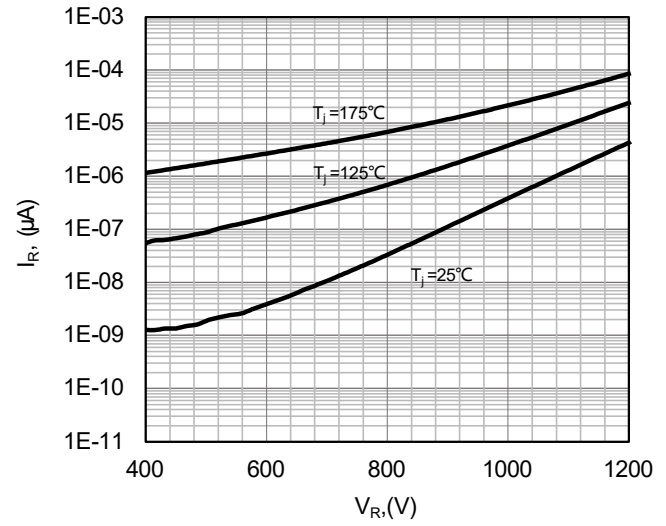


Fig2. Reverse Characteristics

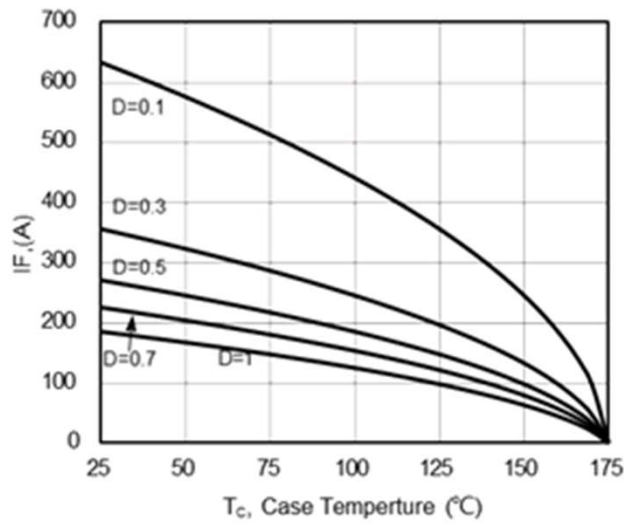


Fig3. Current Derating

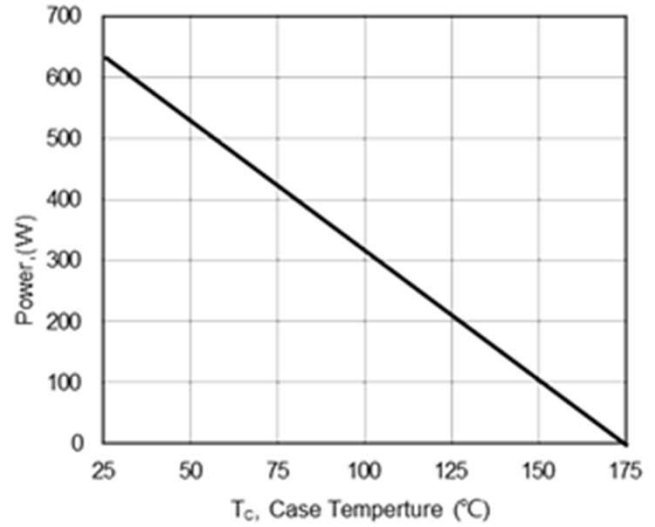


Fig4. Power Derating

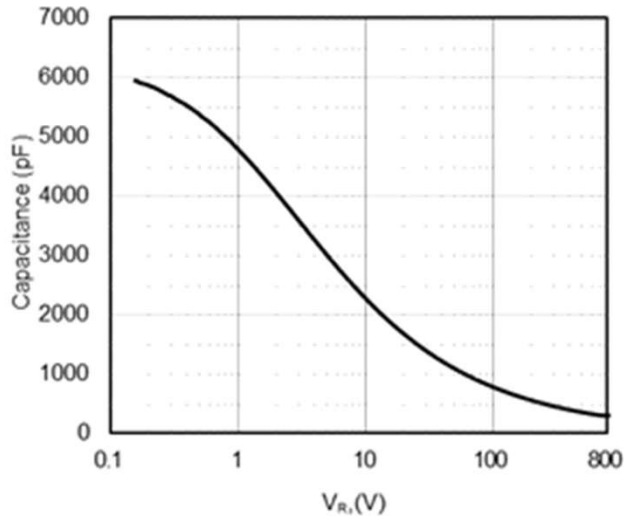


Fig5. Capacitance Characteristics

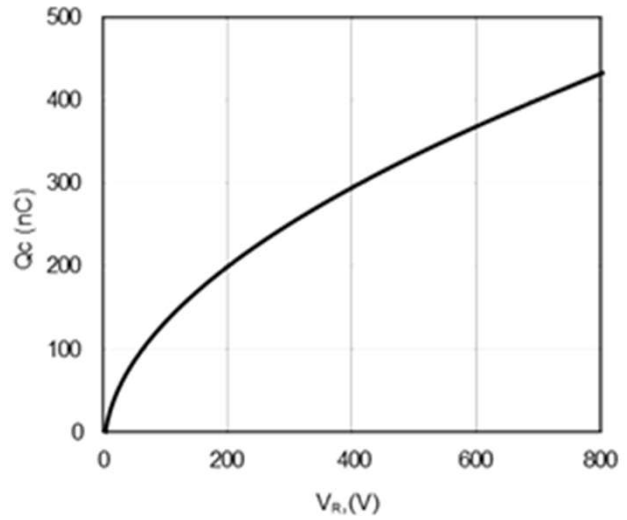


Fig6. Capacitance Charge

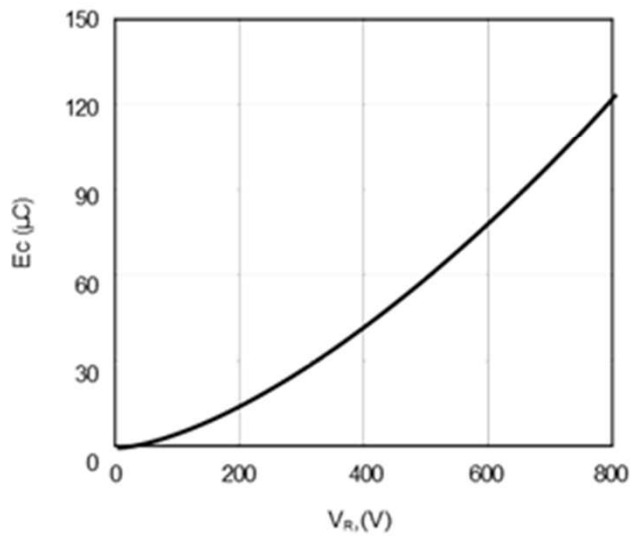


Fig7. Capacitance Stored Energy

Marking Information

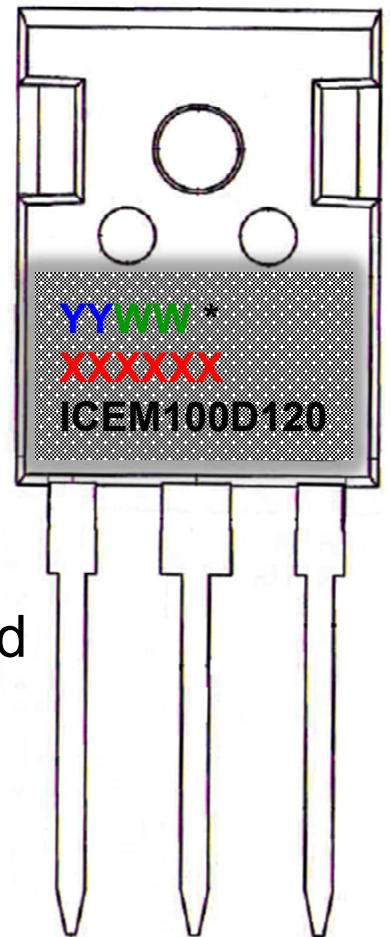
YY = Last two digits of the year

WW = Work week

***** = Site ID

XXXXXX = Lot ID

ICEM100D120 = ICE is Icemos logo and
M100D120 is a designated device part
number



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